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www.ratnerprestia.com**FACSIMILE COVER SHEET**DATE: September 24, 2003OUR REF.: YAO-3950US and YAO-3950US2

TIME: _____

YOUR REF.: 09/103,873 and 10/170,168

| | |
|--------------------|---|
| TO: | Examiner Jose R. Diaz |
| COMPANY: | United States Patent and Trademark Office |
| FROM: | Lawrence E. Ashery |
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| TITLE OF DOCUMENT: | Draft Amendment for Review Only |

Total Number of Pages: 11 (including this form)**COMMENTS****CONFIDENTIAL AND PRIVILEGED ATTORNEY/CLIENT INFORMATION**

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**DRAFT - FOR EXAMINER REVIEW ONLY
NOT FOR FILING**Attorney Docket No. YAO-3950
PATENT

In re Application of

Yoshihisa Nagano et al.

Serial No.: ~~09/103,873~~

Filed: June 24, 1998

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

:
: Group Art Unit: 2815
:
: Examiner: Jose R. Diaz
:
:**AMENDMENT UNDER 37 C.F.R. § 1.111****IN THE CLAIMS:**

Please amend claims 1 and 32 as follows, and add claim 35:

1. (Currently amended) A semiconductor device, comprising:

a capacitor provided on supporting substrate ~~[having an integrated circuit thereon]~~ and including a lower electrode, a dielectric film, and an upper electrode, said dielectric film being formed from ~~[either a dielectric material having a high dielectric constant or]~~ a ferroelectric material;

a first interlayer insulating film provided so as to ~~[directly]~~ cover the capacitor;

¹⁴ a first interconnect selectively provided on the first interlayer insulating film and electrically connected to ~~[the integrated circuit and]~~ the capacitor through a first contact hole formed in the first interlayer insulating film;